

Appl. No.: 10/796,656
Amdt. dated 07/24/2006
Reply to Office action of March 22, 2006

Amendments to the Specification:

Please replace the title of the application with the following amended title:

COMPOSITION FOR FORMING A POROUS FILM PREPARED BY HYDROLYSIS AND CONDENSATION OF AN ALKOXYSLANE USING A TRIALKYLMETHYLAMMONIUM HYDROXIDE CATALYST

Please replace the paragraph beginning on page 5, line 23 and ending on page 6, line 7 with the following amended paragraph:

After an effort to achieve the objects, the inventors has have found that tetraalkylammonium tetraalkylammonium hydroxide obtained by the electrolysis of quaternary ammonium carbeneate carbonate produced by the reaction between trialkylamine and dialkyl carbonate, comprises reduced amounts of alogen and metallic impurities wherein boron is counted in the metallic impurity, and is an excellent basic catalyst in the hydrolysis and condensation reaction of alkoxy silane to produce a silica composition imparting high hardness. Then, they have completed the invention.

Appl. No.: 10/796,656
Amdt. dated 07/24/2006
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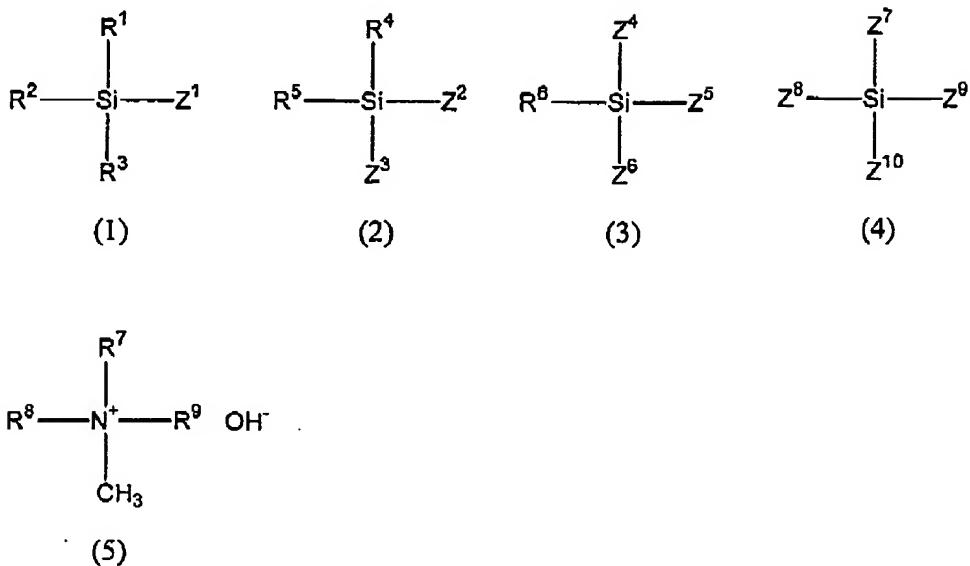
2. (Previously Presented) The composition for forming a porous film according to Claim 1 wherein the total carbon number of R⁷, R⁸ and R⁹ in said trialkylmethyldiammonium hydroxide is 4 to 15.

3. (Previously Presented) The composition for forming a porous film according to Claim 1 wherein said trialkylmethyldiammonium comprises a reaction product of trialkylamine and dimethyl carbonate.

4. (Previously Presented) The composition for forming a porous film according to Claim 1, wherein said hydrolysis and condensation product of an alkoxy silane or the partial hydrolysis product of the alkoxy silane comprises a product having a weight-average molecular weight of 10,000 to 1,000,000.

5. (Previously Presented) A method for manufacturing a composition for forming a porous film, comprising hydrolysing and condensing an alkoxy silane or a partial hydrolysis product of the alkoxy silane in an organic solvent in the presence of trialkylmethyldiammonium hydroxide as a catalyst, wherein the alkoxy silane comprises one or more alkoxy silanes selected from the group consisting of compounds represented by formulae (1) to (4) below, and the trialkylmethyldiammonium hydroxide is represented by formula (5) below which is a reaction product of trialkylamine and dimethyl carbonate,

Appl. No.: 10/796,656
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wherein Z^1 , Z^2 , Z^3 , Z^4 , Z^5 , Z^6 , Z^7 , Z^8 , Z^9 and Z^{10} each independently represents an alkoxy group having 1 to 6 carbons; R^1 , R^2 , R^3 , R^4 , R^5 and R^6 each independently represents a monovalent hydrocarbon group which is optionally substituted; and R^7 , R^8 and R^9 each independently represents an alkyl group having 1 to 6 carbons.

6. (Previously Presented) A method for manufacturing a porous film comprising applying a composition according to Claim 1 to a substrate to form a film thereon, drying the film and heating the dried film to produce a porous film.

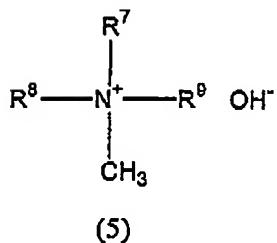
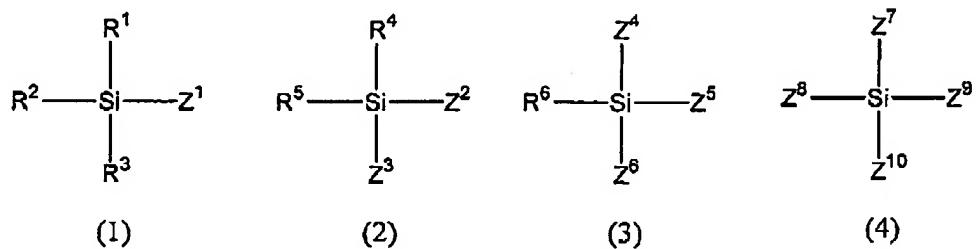
7. (Previously Presented) A porous film comprising a composition according to Claim 1.

8. (Previously Presented) An interlevel insulating film comprising a composition according to Claim 1.

9. (Currently amended) A semiconductor device comprising a porous film therein, the porous film formed of a composition comprising ~~10 ppm~~ 10 ppm or less halogen impurity and

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10 ppb-100 ppb or less metallic impurity where boron is counted in the metallic impurity, the composition comprising the hydrolysis and condensation product of an alkoxy silane or a partial hydrolysis product of the alkoxy silane in an organic solvent in the presence of trialkylmethylammonium hydroxide as a catalyst, wherein the alkoxy silane comprises one or more alkoxy silanes alkoxy silanes selected from the group consisting of compounds represented by formulae (1) to (4) below, and the trialkylmethylammonium hydroxide is represented by formula (5) below,



wherein $Z^1, Z^2, Z^3, Z^4, Z^5, Z^6, Z^7, Z^8, Z^9$ and Z^{10} each independently represents an alkoxy group having 1 to 6 carbons; R^1, R^2, R^3, R^4, R^5 and R^6 each independently represents a monovalent hydrocarbon group which is optionally substituted; and R^7, R^8 and R^9 each independently represents an alkyl group having 1 to 6 carbons.

10. (Previously Presented) The semiconductor device according to Claim 9 wherein the total carbon number of R^7 , R^8 and R^9 in said trialkylmethylammonium hydroxide is 4 to 15.

Appl. No.: 10/796,656
Amdt. dated 07/24/2006
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11. (Previously Presented) The semiconductor device according to Claim 9 wherein said trialkylmethylenammonium hydroxide comprises a reaction product of trialkylamine and dimethyl carbonate.

12. (Previously Presented) The semiconductor device according to Claim 9 wherein said hydrolysis and condensation product of an alkoxy silane or the partial hydrolysis product of the alkoxy silane comprises a product having a weight-average molecular weight of 10,000 to 1,000,000.

13. (Previously Presented) The semiconductor device according to Claim 9 wherein said porous film is between metal interconnections in a same layer or multi-level interconnects, or is between upper and lower metal interconnection layers.